## **PNA2602M**

### **Darlington Phototransistor**

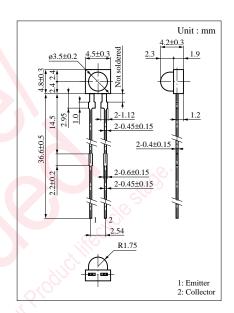
For optical control systems

#### Features

- Darlington output, high sensitivity
- Easy to combine light emission and photodetection on same printed circuit board
- Small size, thin side-view type package
- Long lead and visible light cutoff design with PN205



| Parameter                     | Symbol           | Ratings       | Unit |
|-------------------------------|------------------|---------------|------|
| Collector to emitter voltage  | V <sub>CEO</sub> | 20            | V    |
| Emitter to collector voltage  | V <sub>ECO</sub> | 5             | V    |
| Collector current             | $I_{C}$          | 30            | mA   |
| Collector power dissipation   | P <sub>C</sub>   | 100           | mW   |
| Operating ambient temperature | T <sub>opr</sub> | -25 to +80    | °C   |
| Storage temperature           | T <sub>stg</sub> | -30  to  +100 | °C   |

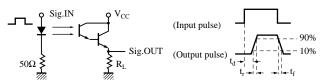


### ■ Electro-Optical Characteristics (Ta = 25°C)

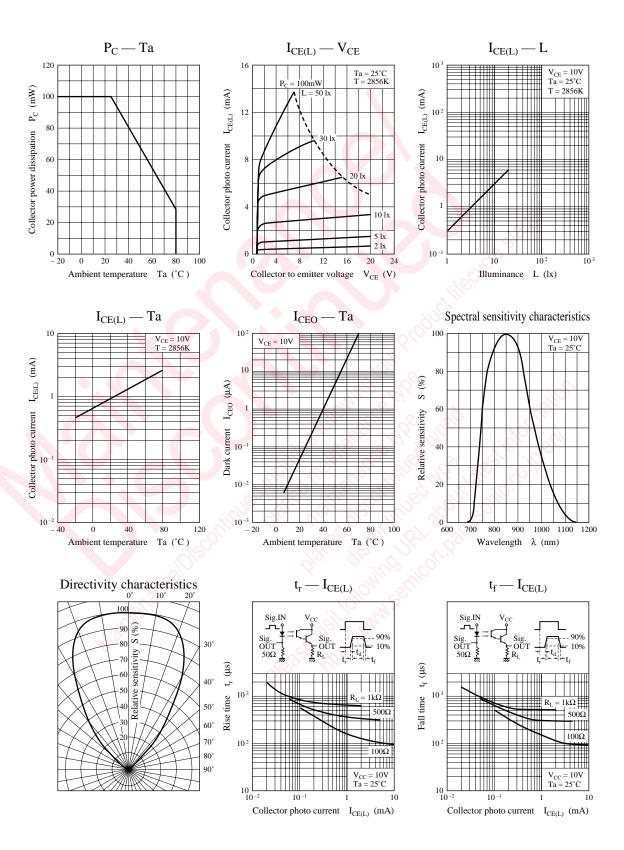
| Parameter                        | Symbol                  | Conditions   | min | typ | max | Unit |
|----------------------------------|-------------------------|--|-----|-----|-----|------|
| Dark current                     | $I_{CEO}$               | $V_{CE} = 10V$   | 9.  |     | 0.5 | μΑ   |
| Sensitivity to infrared emitters | S <sub>IR</sub> *1      | $V_{CE} = 10V, H = 3.75 \mu\text{W/cm}^2$              | 0.1 |     | 3.0 | mA   |
| Peak sensitivity wavelength      | $\lambda_{\mathrm{P}}$  | $V_{CE} = 10V$   |     | 850 |     | nm   |
| Acceptance half angle            | θ                       | Measured from the optical axis to the half power point |     | 35  |     | deg. |
| Response time                    | $t_r, t_f^{*2}$         | $V_{CC} = 10V, I_{C} = 1 \text{mA}, R_{L} = 100\Omega$ |     | 150 |     | μs   |
| Collector saturation voltage     | V <sub>CE(sat)</sub> *1 | $I_C = 100 \mu A, H = 3.75 \ \mu W/cm^2$               |     |     | 1.5 | V    |

<sup>\*1</sup> Measurements were made using infrared light ( $\lambda = 940$  nm) as a light source.

<sup>\*2</sup> Switching time measurement circuit



- t<sub>d</sub>: Delay time
- t<sub>r</sub>: Rise time (Time required for the collector photo current to increase from 10% to 90% of its final value)
- $t_{\rm f}$ : Fall time (Time required for the collector photo current to decrease from 90% to 10% of its initial value)



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